

Amendments to the Abstract

Please amend the Abstract of the Disclosure as follows:

A chemical vapor deposition (CVD) method apparatus for depositing a silicide ~~and a CVD system for performing the same are~~ is disclosed. After a substrate is loaded in a load-lock chamber, the substrate is transferred into a processing chamber. A silicide is deposited on [[a]] the substrate. After the substrate is transferred into the load-lock chamber, Residual residual gases remaining from the ~~depositing step on the substrate are~~ purged out by flowing air including H₂O (g) from an air purge line connected to the load-lock chamber. ~~to substantially remove fumes caused by the residual gases.~~ The purged residual gases are exhausted by a vacuum pump connected to the air purge line. ~~In the purge step, the cycle purge is carried out at the conditions similar to the flow of atmosphere,~~ ~~to substantially remove the fumes.~~